

Title (en)
METHOD RELATING TO ANODIC BONDING

Title (de)
METHODE FÜR ANODISCHES BONDEN

Title (fr)
PROCEDE CONCERNANT LES LIAISONS ANODIQUES

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Application
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Abstract (en)
[origin: WO0129890A2] The present invention relates to a method of bonding a first member (110, 210, 130, 230, 410, 430, 510, 530, 610) to a second silicon member (120, 220, 420a, 420b, 600) through anodic bonding. The method comprises the steps of selectively depositing on said first member bondable sections (170a, 170b, 270, 470a, 470b, 470c, 570, 620) before bringing said first and second members together for anodic bonding.

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